

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2984580	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 17:55
L2	7844	1 and cell with source with float\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:04
L3	8716	1 and cell with (source or drain) with float\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:05
L4	63	1 and cell with second adj transistor with (source or drain) with float\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:11
L5	493	3 not floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:11
L6	186	5 and cell with transistor with (source or drain) with float\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:11
L7	18	5 and cell with (second or first) adj3 transistor with (source or drain) with float\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:30
L8	6	5 and cell with transistor with series with (source or drain) with float\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:33
L9	369150	1 and cell not floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:35
L10	166	9 and cell with transistor with source with float\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:36
L11	10	10 and second adj transistor with cell	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:43
L12	3877	reduc\$5 with leak\$5 with cell	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:44

L13	9	11 and (writ\$5 or program\$5) with cell	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:46
L14	1379	12 and (writ\$5 or program\$5) with cell	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:46
L15	5	14 and ground with gate with first adj transistor with cell	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:48
L16	5	15 and (voltage or potential) with source with first adj2 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:55
L17	51443	writ\$5 with cell	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:56
L18	45	17 and ground with gate with first adj transistor with cell	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:57
L19	9	18 and reference with source with first adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:59
L20	9	19 and second adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 18:59
L21	6	19 and second adj transistor with cell	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 19:01
L22	5	21 and leak\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/19 19:02